

AXIAL LEADED SILICON RECTIFIER DIODES

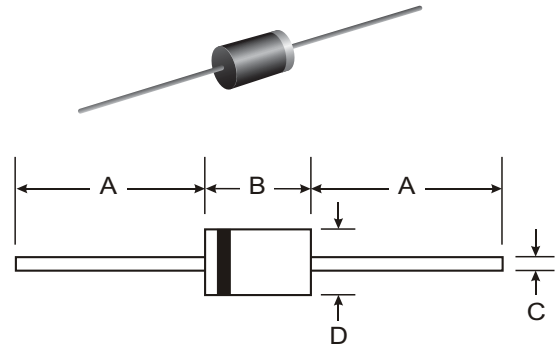
VOLTAGE RANGE: 400V
CURRENT: 1.0 A

Features

- Miniature Size
- Low Forward Voltage drop
- Low Reverse Leakage Current
- High Surge Capability
- 52mm Inside Tape Spacing Package Available

Mechanical Data

- Case: D O - 4 1 Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-41		
Dim	Min	Max
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

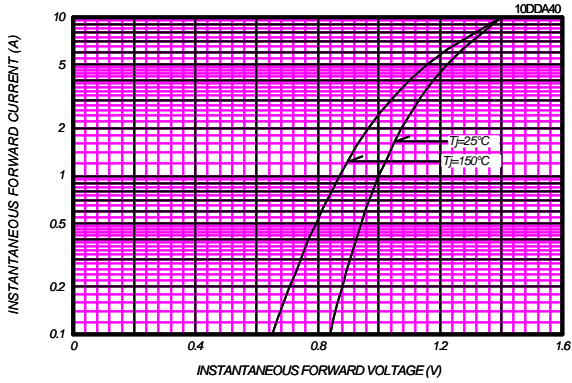
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Rating	Symbol	10DDA40		Unit
Repetitive Peak Reverse Voltage	V_{RRM}	400		V
Average Rectified Output Current	I_o	50Hz Half Sine Wave Resistive Load	$T_a=58^\circ\text{C} *1$ $T_l=132^\circ\text{C}$ (T_l =Lead Temperature)	1.0 A
RMS Forward Current	$I_{F(RMS)}$			1.57 A
Surge Forward Current	I_{FSM}	50Hz Half Sine Wave, 1cycle, Non-repetitive		45 A
Operating Junction Temperature Range	T_{jw}	- 40 to + 150		$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 150		$^\circ\text{C}$

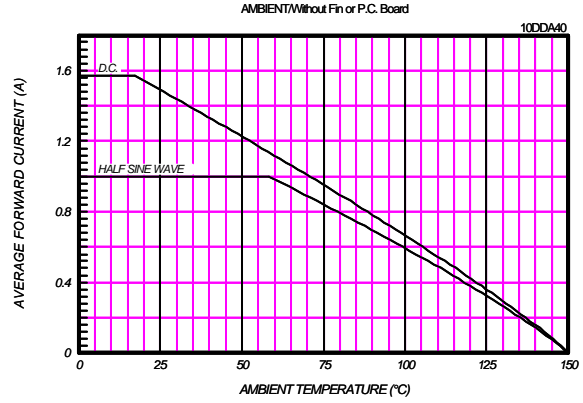
Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j = 25^\circ\text{C}$, $V_{RM} = V_{RRM}$	-	-	10	μA
Peak Forward Voltage	V_{FM}	$T_j = 25^\circ\text{C}$, $I_{FM} = 1.0\text{A}$	-	-	1.0	V
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient *1			91	$^\circ\text{C/W}$
	$R_{th(j-l)}$	Junction to Lead			17	

*1: Without Fin or P.C. Board mounted

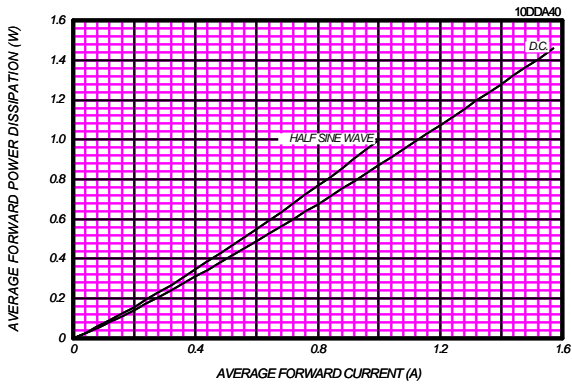
FORWARD CURRENT VS. VOLTAGE



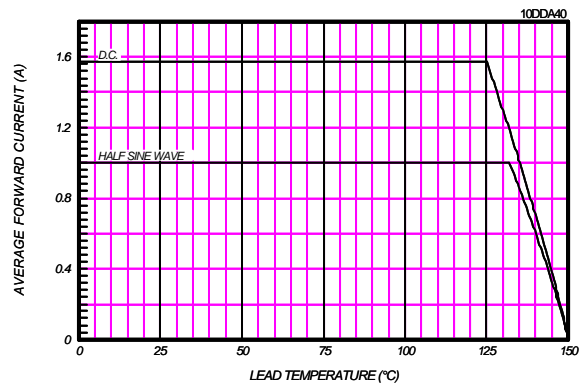
AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE



AVERAGE FORWARD POWER DISSIPATION

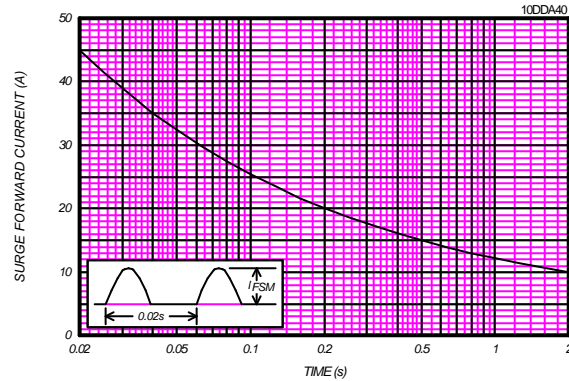


AVERAGE FORWARD CURRENT VS. LEAD TEMPERATURE



SURGE CURRENT RATINGS

$f = 50\text{Hz}$, Half Sine Wave, Non-Repetitive, No Load



单击下面可查看定价，库存，交付和生命周期等信息

[>>SUNMATE\(森美特\)](#)